

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	537	257/754.ccls.	US- PGPUB; USPAT; USOCR
2	BRS	L2	1127	257/750.ccls.	US- PGPUB; USPAT; USOCR
3	BRS	L3	1044	257/763.ccls.	US- PGPUB; USPAT; USOCR
4	BRS	L4	529	257/764.ccls.	US- PGPUB; USPAT; USOCR
5	BRS	L5	392	257/768.ccls.	US- PGPUB; USPAT; USOCR
6	BRS	L6	353	257/770.ccls.	US- PGPUB; USPAT; USOCR
7	BRS	L7	221	257/754.ccls.	EPO; JPO; DERWENT; IBM_TDB
8	BRS	L8	222	257/750.ccls.	EPO; JPO; DERWENT; IBM_TDB
9	BRS	L9	364	257/763.ccls.	EPO; JPO; DERWENT; IBM_TDB
10	BRS	L10	74	257/764.ccls.	EPO; JPO; DERWENT; IBM_TDB

11	BRS	L11	43	257/768.ccls.	EPO; JPO; DERWENT; IBM_TDB
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	Type	L #	Hits	Search Text	DBs
12	BRS	L12	42	257/770.ccls.	EPO; JPO; DERWENT; IBM_TDB
13	BRS	L14	13	L2 and (titanium with silicide) and dopant and resistance and (react\$3 or anneal\$3 or heat\$3) and ohm\$2	US-PGPUB; USPAT; USOCR
14	BRS	L16	21	L4 and (titanium with silicide) and dopant and resistance and (react\$3 or anneal\$3 or heat\$3) and ohm\$2	US-PGPUB; USPAT; USOCR
15	BRS	L17	14	L5 and (titanium with silicide) and dopant and resistance and (react\$3 or anneal\$3 or heat\$3) and ohm\$2	US-PGPUB; USPAT; USOCR
16	BRS	L18	1	(semiconductor and (titanium with silicide) and dopant and resistance and (react\$3 or anneal\$3 or heat\$3) and ohm\$2).clm.	US-PGPUB
17	BRS	L13	19	L1 and (titanium with silicide) and dopant and resistance and (react\$3 or anneal\$3 or heat\$3) and ohm\$2	US-PGPUB; USPAT; USOCR
18	BRS	L15	14	L3 and (titanium with silicide) and dopant and resistance and (react\$3 or anneal\$3 or heat\$3) and ohm\$2	US-PGPUB; USPAT; USOCR

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19	BRS	L19	1	(semiconductor and (titanium with silicide) and dopant and resistance and (react\$3 or anneal\$3 or heat\$3) and ohm\$2 and width).clm.	US-PGPUB